

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

NUS-03-001

Application Number

101802,563

Applicant

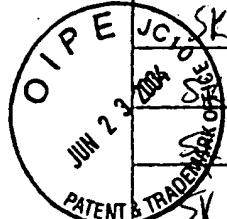
Hong Yun Yu et al.

Filing Date

03/17/04

Group Art Unit

U. S. PATENT DOCUMENTS



EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
SK	62251685/1/01		Gardner et al.	438	287	6/4/98
SK	63838795/7/02		Kizilgalli et al.	438	303	5/17/00
SK	65119111/28/03		Besser et al.	438	656	4/3/01
SK	66176249/9/03		Powell	257	288	3/15/01
SK	60431573/28/00		Gardner et al.	438	692	12/18/97
SK	59602709/28/99		Misra et al.	438	197	8/11/97
SK	60838367/4/00		Rodder	438	690	12/18/98
SK	65769676/10/03		Schaeffer, III et al.	257	411	9/18/00
SK	647936211/12/02		Cunningham	438	369	2/14/01
SK	62080043/27/01		Cunningham	257	413	8/19/98
SK	60514874/18/00		Gardner et al.	438	585	12/18/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Published Pages, Etc.)

SK	-	Heuss et al., Abstract C7.6 "Thermal Stability of Hafnium and Hafnium Nitride (HfN _x) Gate Electrodes on Silicon Dioxide," pp. 67, 76-77, Materials Res. Soc. Proc. April 2000.
SK	-	"Physical and Electrical Properties of Metal Gate Electrodes on HfO ₂ Gate Dielectrics," by J.K. Schaeffer et al., Journal of Vacuum Science and Tech., Vol. 21(1), Jan/Feb 2003, pp. 11-17.

EXAMINER	DATE CONSIDERED
	5/23/08

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Doctor Number (Specie) NUS - 03 - 001	Application Number 10/802,563
	Applicant <i>Hong Yun Yu et al.</i>	
	Filing Date 03/17/04	Drawn At Llnr

U. S. PATENT DOCUMENTS

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OTHER DOCUMENTS (including Author, Title, Date, References, Pages, Etc.)

SK	<p>- "Thermal Stability of PVD TiN Gate and Its Impacts on Characteristics of CMOS Transistors," by M. Wang et al., 6th Int'l Symp. on Plasma Process Induced Damage, May 14-15, 2001, Monterey, CA, USA, pp. 36-39.</p>
SKC	<p>- "Metal Gates for Advanced Sub-80-nm SOI CMOS Technology," by B. Cheng et al., 2001 IEEE Int'l SOI Conf., 10/01, pp. 91-92.</p>

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Hong Yu Yu et al.

Filing Date 03/17/04

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						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Permanent Pages, Etc.)

SK	- "Properties and Microelectronic Applications of Thin Films of Refractory Metal Nitrides", by M. Wittner, Jr. al. of Vacuum Science Tech. A, Vol. 3, pp. 1797-1803.
SK	- "Int'l Tech. Roadmap for Semiconductor", Semiconductor Industry Association, San Jose, CA (ITRS-2003).

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NUS-03-001

10/802, 563

Applicant Hong Yu Yu et al.

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Portion of Page, Etc.)

SK	-	US Patent App. Pub. US 2003/0197230 A1 to Mocuta et al., Pub. Date 10/23/03, Filed 04/19/02, US Class 257/407.
SK	-	US Patent App. Pub. US 2002/0037615 A1 to Matsuo, Pub. Date 03/28/02, Filed 09/25/01, US Class 438/241.
SK		

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